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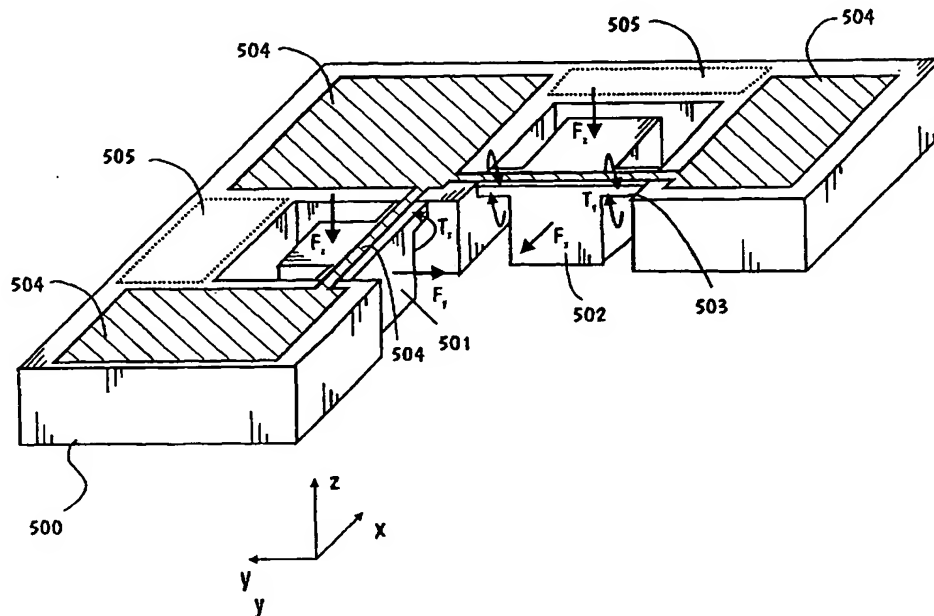
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(54) Title: ACCELERATION SENSOR



(57) **Abstract:** The present invention relates to a low-cost breakable inertial threshold sensor using mainly micro-machining silicon technology. The sensor is constructed on a silicon-wafer or on some other brittle material according to the MEMS process. The sensor comprises a first body portion, a second body portion, and detecting means for giving an indication if the second body portion has damaged the detecting means. The status of the sensor can be read in various ways. In one embodiment the status is remotely readable.

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